

JST100IS-1200BW 100A TRIAC

Rev.A.1.1

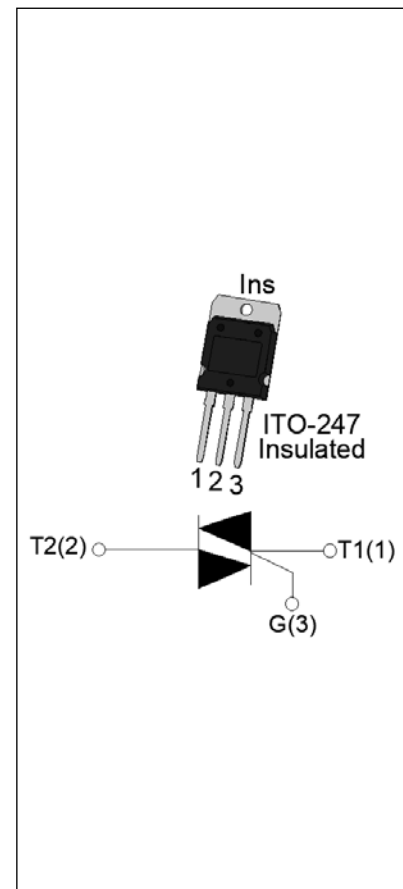
DESCRIPTION:

The JST100IS-1200BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers.

JST100IS-1200BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST100IS-1200BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package ITO-247 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	100	A
V_{DRM}/V_{RRM}	1200	V
$I_{GT\ I/II/III}$	50/50/50	mA


ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	V
RMS on-state current ($T_c \leq 30^\circ\text{C}$)	$I_{T(RMS)}$	100	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	950	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		1045	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	4513	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	25	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG. 7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	I - II - III	MAX.	50	mA
V_{GT}		I - II - III	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3k\Omega$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	180	mA
		II		180	
I_H	$I_T=1A$		MAX.	100	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125^\circ C$		MIN.	2000	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$ $T_j=125^\circ C$		MIN.	25	A/ms
t_{on}	$I_G=100mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25^\circ C$		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=150A$ $t_p=3100\mu s$	$T_j=25^\circ C$	1.8	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.67	V
R_D	Dynamic resistance	$T_j=125^\circ C$	7.5	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	15	μA
I_{RRM}		$T_j=125^\circ C$	12	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	0.6	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (AC)	45	$^\circ C/W$

ORDERING INFORMATION

<u>J</u>	<u>ST</u>	<u>100</u>	<u>IS</u>	<u>-1200</u>	<u>BW</u>
JieJie Microelectronics Co., Ltd.	Triacs				
	$I_{T(RMS)}:100A$				
			IS:ITO-247(Ins)		
					BW:IGT1-3 $\leq 50mA$
				1200: $V_{DRM}/V_{RRM} \geq 1200V$	

MARKING

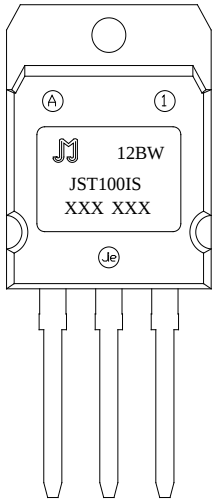
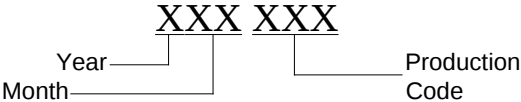
	
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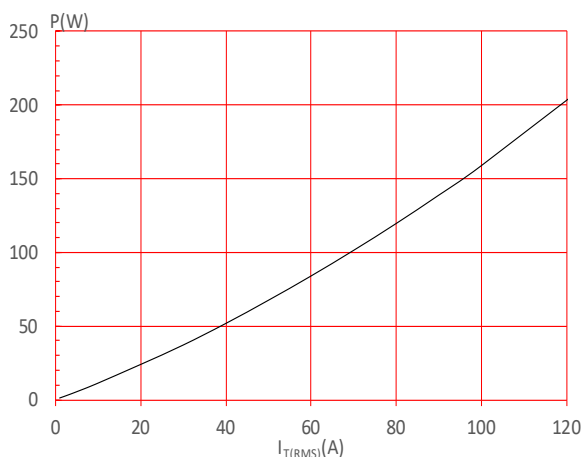
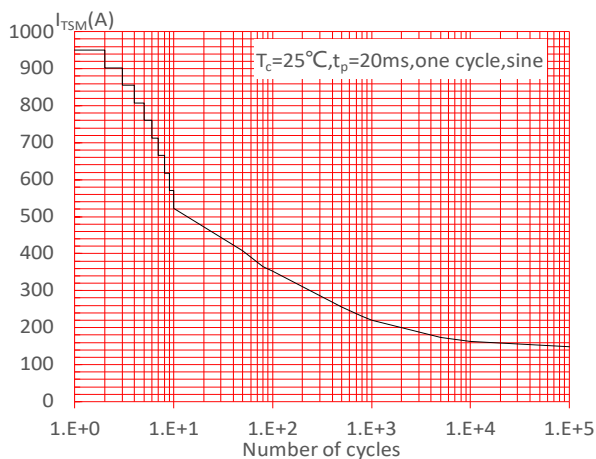
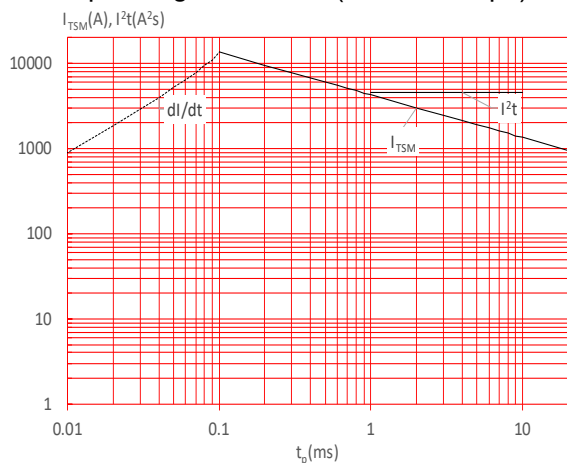
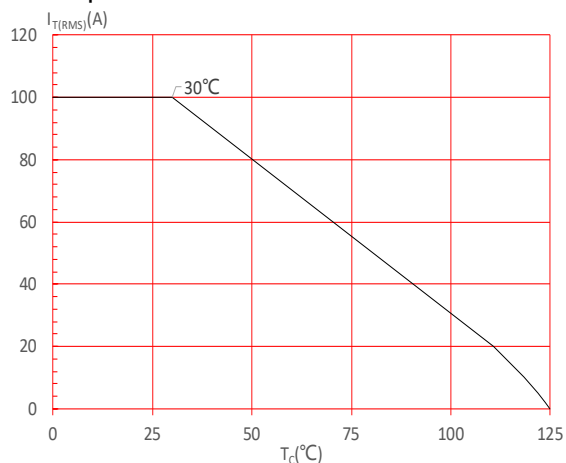
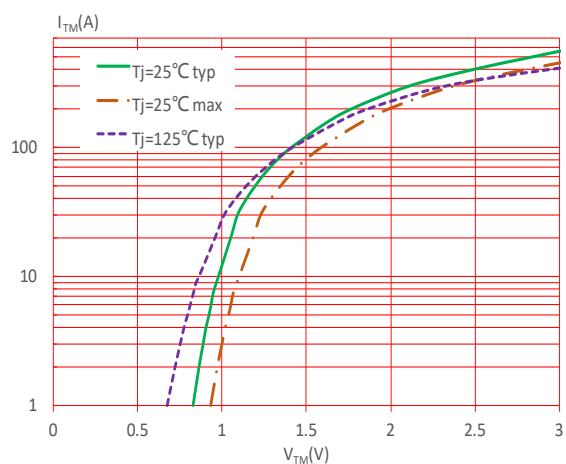
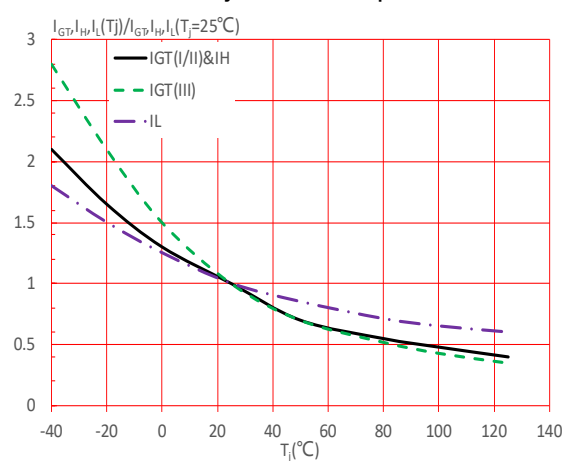
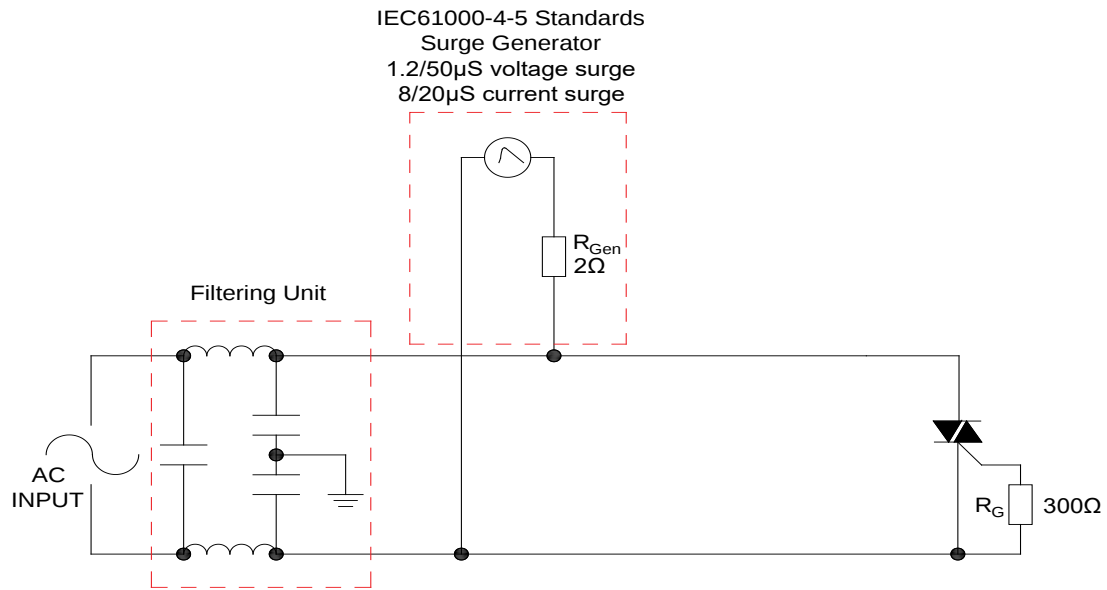
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 100A/\mu s$)

FIG.2: RMS on-state current versus case temperature

FIG.4: On-state characteristic

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}(\text{V})$	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST100IS-1200BW	1200	50	ITO-247(Ins)	25	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

Technical drawing of a 16-pin DIP package showing top, side, and end views with dimensions A through L and A1, B1.

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	19.70		20.10	0.776		0.791
A1	1.10		1.50	0.043		0.059
B	26.90		27.30	1.059		1.075
B1	2.65		3.05	0.104		0.120
C	19.40		20.40	0.764		0.803
D	3.80		4.00	0.150		0.157
E	2.56		2.76	0.101		0.109
F	1.66		1.86	0.065		0.073
G	5.25		5.65	0.207		0.222
H	5.05		5.50	0.199		0.217
I	5.60		6.00	0.220		0.236
J	1.45		1.55	0.057		0.061
K	2.20		2.40	0.087		0.094
L	0.60		0.80	0.024		0.031
M	21.20		21.40	0.835		0.843
N	9.70		10.30	0.382		0.406
O	2.60		3.20	0.102		0.126
Q	15.80		16.20	0.622		0.638

Technical drawing of a mechanical part, showing front, side, and cross-sectional views with dimensions.

Front View (Left):

- Overall width: 508.0 ± 0.2
- Overall height: 30.0 (divided into two 15.0 sections).
- Central feature: A square hole with a textured fill, surrounded by a circular pattern.
- Bottom feature: Four vertical slots.
- Right side feature: A circular hole with diameter $\phi 3 \pm 0.05$.

Side View (Middle):

- Overall width: 532 ± 0.5
- Overall height: 30.0 (divided into two 15.0 sections).
- Right side feature: A circular hole with diameter $\phi 6 \pm 0.1$.

Cross-sectional View (Right):

- Overall height: 51.40 ± 0.2
- Top flange thickness: 7.5 ± 0.2
- Top flange width: 1.2
- Top flange hole diameter: 1.7
- Top flange hole position: 7.5 from the right edge.
- Top flange hole diameter: $0.7^{+0.1}_0$
- Top flange hole position: 2.1 from the left edge.
- Top flange hole diameter: 2.2
- Top flange hole position: 2.2 from the right edge.
- Top flange hole diameter: 0.7

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
ITO-247	TUBE	25	400	1,600

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